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(54) A semiconductor laser device.

(57) A semiconductor laser device of the present invention includes: a semiconductor substrate (8) having a top face and a bottom face; a multi-layered structure formed on the top face of the semiconductor substrate (8), the multi-layered structure including an active layer (7); a stripe-shaped ridge portion (6, 11) which is formed on a first region of a top face of the multi-layered structure and which extends along a cavity length direction; a current blocking layer (9, 10) which covers both side faces of the ridge portion (6, 11) and a second region of the top face of the multi-layered structure; a first electrode (13) formed at least on a top face of the ridge portion (6, 11); and a second electrode (12) formed on the bottom face of the semiconductor substrate (8), wherein the current blocking layer (9, 10) includes an insulating film (9) and a resin film (10) formed on the insulating film (9).

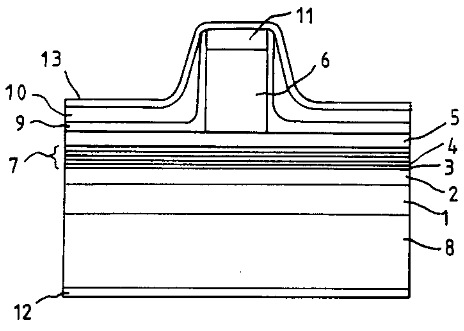

FIG.1.

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Rank Xerox (UK) Business Services
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EUROPEAN SEARCH REPORT

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DOCUMENTS CONSIDERED TO BE RELEVANT

Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.5)
X A	US-A-5 088 099 (CHEN ET AL.) 11 February 1992 * column 5, line 31 - line 52 * * column 3, line 29 - line 41; figures 2,11,12 *	1,2,7-9 3-6	H01S3/19
A	JOURNAL OF APPLIED PHYSICS vol. 63, no. 3 , 1 February 1988 , WOODBURY, US pages 964 - 966 XP115341 F. SATO ET AL. 'Low Thermal Expansion Polymide Buried Ridge Waveguide AlGaAs/GaAs Single-Quantu-Well Laser Diode'	1,2,7-9	
A	ELECTRONICS LETTERS vol. 25, no. 10 , 11 May 1989 , STEVENAGE, GB pages 668 - 669 XP112465 K. UOMI ET AL. 'Ultrahigh-Speed 1.55um lambda/4-Shifted DFB PIQ-BH Lasers with Bandwidth of 17GHz' * page 668, right column, line 4 - line 10; figure 1 * * abstract *	2-6	TECHNICAL FIELDS SEARCHED (Int.Cl.5) H01S
A	EP-A-0 385 388 (OMRON) 5 September 1990 * column 2, line 51 - column 4, line 5; figure 1 *	10,12	

The present search report has been drawn up for all claims

Place of search	Date of completion of the search	Examiner
THE HAGUE	5 January 1994	Stang, I

CATEGORY OF CITED DOCUMENTS

X : particularly relevant if taken alone
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